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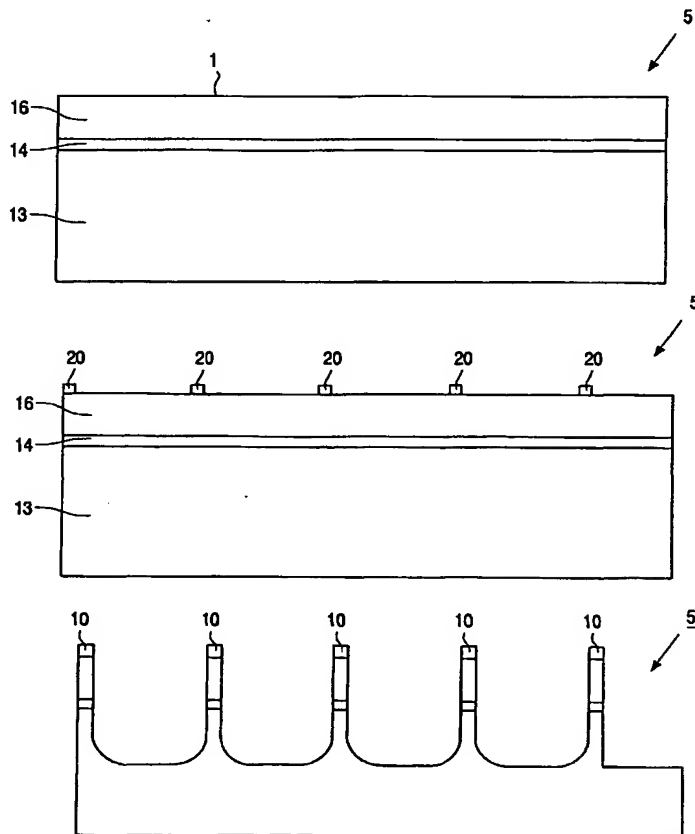
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(54) Title: METHOD OF MANUFACTURING NANOWIRES AND ELECTRONIC DEVICE



(57) Abstract: In the method, semiconductor substrates are etched to provide nanowires, said substrates comprising a first layer of a first material and a second layer of a second material with a mutual interface, which first and second materials are different. They may be different in the doping type. Alternatively, the main constituent of the material may be different, for example SiGe or SiC versus Si, or InP versus InAs. In the resulting nanowires, the interface is atomically sharp. The electronic devices having nanowires between a first and second electrode accordingly have very good electroluminescent and optoelectronic properties.



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INTERNATIONAL SEARCH REPORT

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A. CLASSIFICATION OF SUBJECT MATTER

IPC 7 H01L21/306 H01L21/3063 H01L21/3065 H01L21/308 H01L29/12
H01L33/00

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

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Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, INSPEC

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	EP 0 544 408 A (XEROX CORP) 2 June 1993 (1993-06-02)	1-4,8,9
Y	column 8-10; figures 3-7 ---	7
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Y	page 176, right-hand column; figure 1 --- -/--	7



Further documents are listed in the continuation of box C.



Patent family members are listed in annex.

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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

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